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2N2779 (#22998)

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Overview

Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			1.50	V
DC Current Gain	HFE	10.00			

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			250.00	V
Collector Current (dc)	I_C			30.00	A
Collector-Emitter Voltage (Base Open)	V_{CEO}			250.00	V
Emitter-Base Voltage (Collector Open)	V_{EBO}			15.00	V
Power Dissipation, Total	P_T			200.00	W

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